CRMITL20570A

N-Channel 200V,478mΩ Typ. Power MOSFET

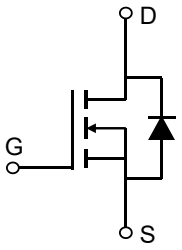
Description

Features

- 200V, 5A

  $R_{DS(ON)}$ Typ = 478mΩ @ V_{GS} = 10V

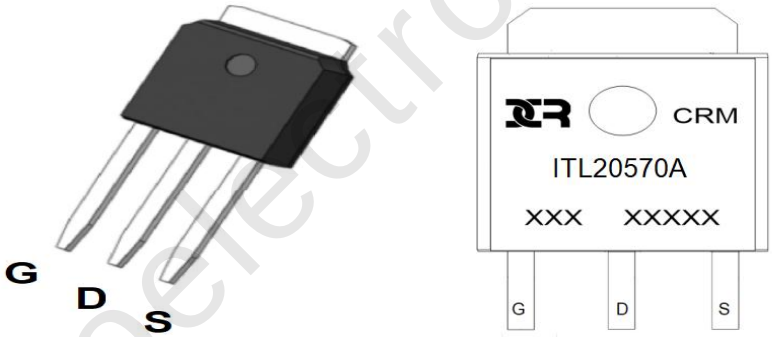
  Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔVds TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	TUBE(pcs)	Inner Box (pcs)	Per Carton (pcs)
CRMITL20570A	CRMITL20570A	TO-251-3L	TUBE	72	4320	21600

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		200	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	5	A
		T_C = 100°C	3	A
I_{DM}	Pulsed Drain Current [1]		20	A
E_{AS}	Single Pulsed Avalanche Energy [2]		26.5	mJ
P_D	Power Dissipation	T_C = 25°C	35	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		3.6	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	200	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 200V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.2	1.8	2.4	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 3A	-	478	573	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz	-	625	-	pF
C_{oss}	Output Capacitance		-	32	-	pF
C_{rss}	Reverse Transfer Capacitance		-	23	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, V_{DS} = 100V, I_D =1A	-	12	-	nC
Q_{gs}	Gate Source Charge		-	2.5	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	3.8	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 100V, I_D= 1A, R_{GEN} = 2.5Ω	-	10	-	ns
t_r	Turn-On Rise Time		-	12	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	15	-	ns
t_f	Turn-Off Fall Time		-	15	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 3A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 1A, di/dt = 100A/us	-	50	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	98	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25ohm, L=10mH, I_{AS}=2.3A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

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Test Circuit

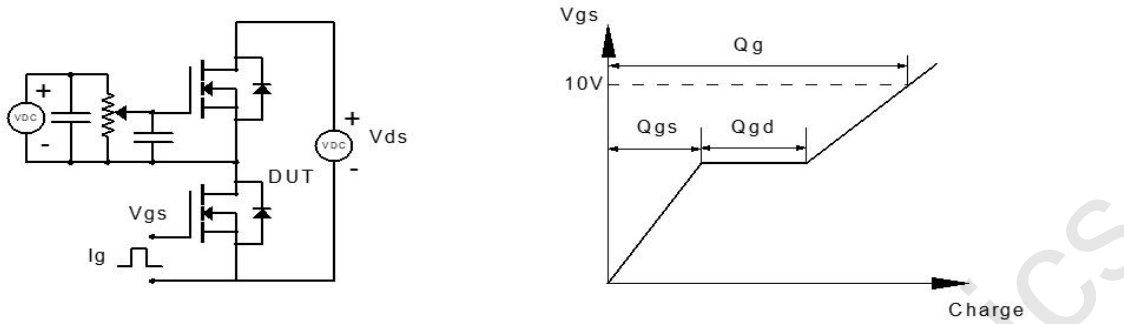

Figure 1: Gate Charge Test Circuit & Waveform

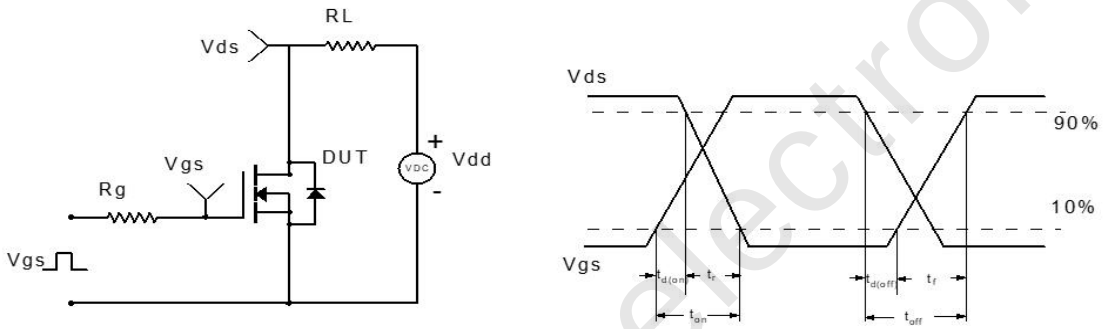

Figure 2: Resistive Switching Test Circuit & Waveform

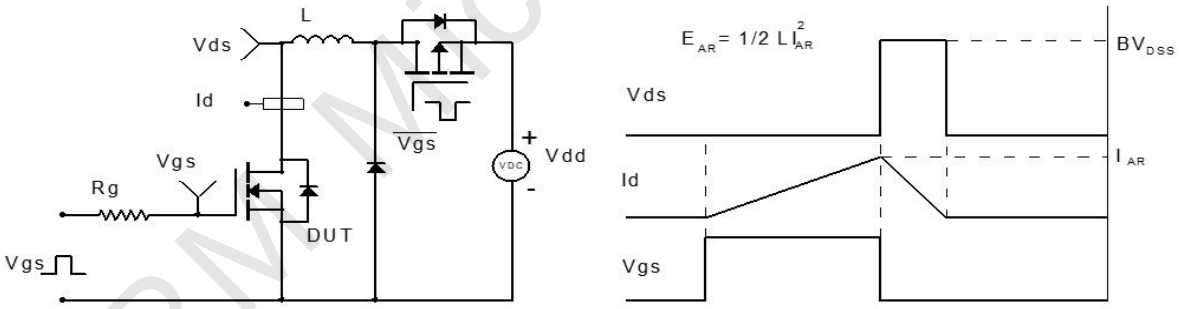

Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

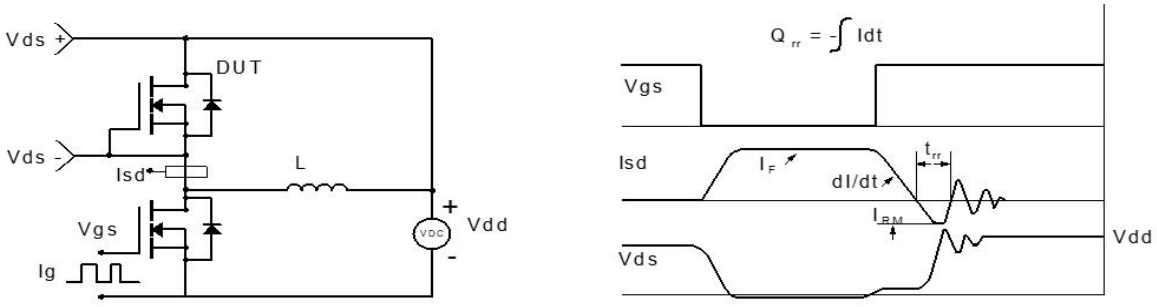

Figure 4: Diode Recovery Test Circuit & Waveform

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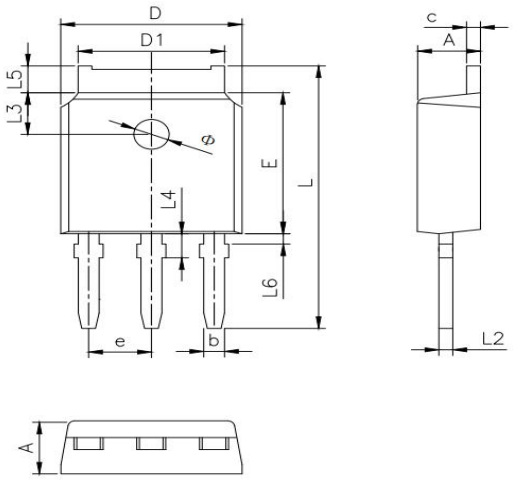
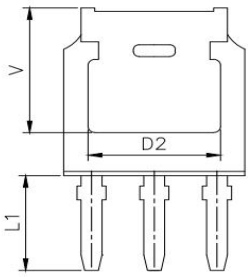
Package Mechanical Data(TO-251-3L)





SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.20	2.30	2.40
b	0.66	0.76	0.86
c	0.46	0.51	0.58
D	6.50	6.60	6.70
D1	5.10	5.33	5.46
D2	4.83 REF.		
E	6.00	6.10	6.20
e	2.19	2.29	2.39
L	11.02	11.22	11.42
L1	4.10 REF.		
L2	0.508BSC		
L3	1.80 REF.		
L4	0.95	1.05	1.15
L5	0.90	--	1.25
L6	0.15	--	0.75
Φ	1.10	--	1.30
V	5.40 REF		

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